



NTB125N02RT4G Information



For Reference Only

Part Number NTB125N02RT4G
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 24V 15.9A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NTB125N02RT4G Specifications

Manufacturer Part Number NTB125N02RT4G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 24V Current - Continuous Drain (Id) @ 25°C 95A (Ta), 120.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 28nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 3440pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.98W (Ta), 113.6W (Tc) Pds On (Max) @ Id Vgs 4.6 mOhm @ 20A, 10V		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)24VCurrent - Continuous Drain (Id) @ 25°C95A (Ta), 120.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs28nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3440pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.98W (Ta), 113.6W (Tc)	Manufacturer Part Number	NTB125N02RT4G
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Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 95A (Ta), 120.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Current - Continuous Drain (Id) @ 25°C 95A (Ta), 120.5A (Tc) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 3440pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.98W (Ta), 113.6W (Tc)	Series	-
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Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 28nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 3440pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.98W (Ta), 113.6W (Tc)	Drain to Source Voltage (Vdss)	24V
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Input Capacitance (Ciss) (Max) @ Vds 3440pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.98W (Ta), 113.6W (Tc)	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max) $\pm 20 \text{V}$ FET Feature-Power Dissipation (Max) 1.98W (Ta), 113.6W (Tc)	Gate Charge (Qg) (Max) @ Vgs	28nC @ 4.5V
FET Feature - Power Dissipation (Max) 1.98W (Ta), 113.6W (Tc)	Input Capacitance (Ciss) (Max) @ Vds	3440pF @ 20V
Power Dissipation (Max) 1.98W (Ta), 113.6W (Tc)	Vgs (Max)	±20V
-	FET Feature	-
P.ds On (May) @ Id Vas	Power Dissipation (Max)	1.98W (Ta), 113.6W (Tc)
Kus Oli (Max) @ Iu, vgs 4.0 IIIOIIII @ 20A, 10 v	Rds On (Max) @ Id, Vgs	4.6 mOhm @ 20A, 10V
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package D2PAK	Supplier Device Package	D2PAK
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
Report errors?		Report errors?

NTB125N02RT4G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTB125N02RT4G Payment Methods



















NTB125N02RT4G Shipping Methods













If you have any question about NTB125N02RT4G, please do not hesitate to contact us!

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